



--	--	--	--	--



	°C					
	°C					
	°C					
	°C					
	°C					
	°C					
	°C					

FIG.1: Power dissipation vs. on-state current
(per thyristor or diode)

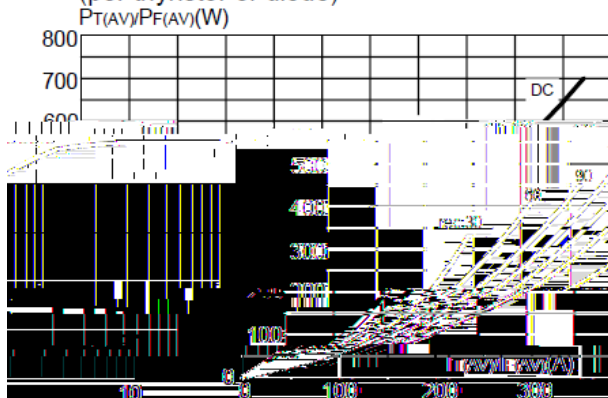


FIG.2: Maximum transient thermal impedance
junction to case(per thyristor or diode)

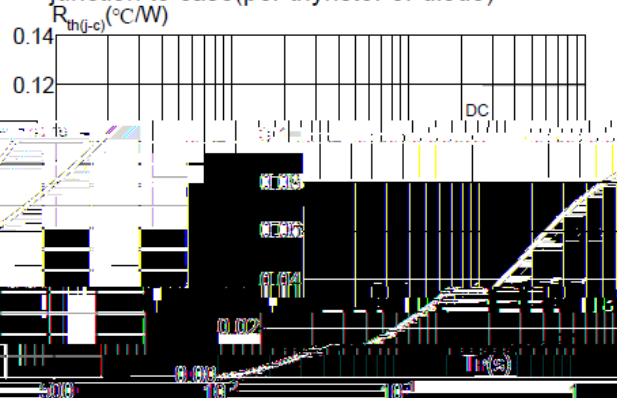


FIG.3: Forward characteristics
(per thyristor or diode)

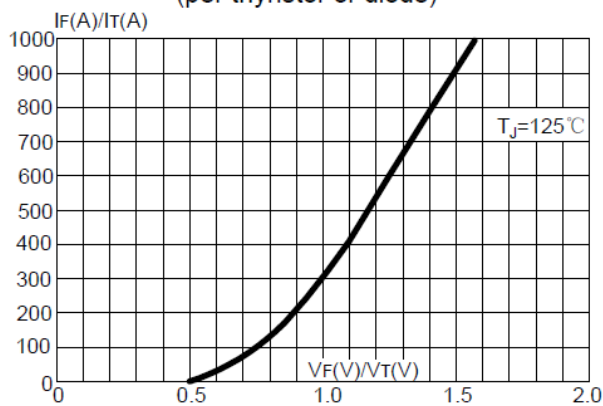


FIG.4: Relative variations of gate trigger current, holding current and latching current versus junction temperature

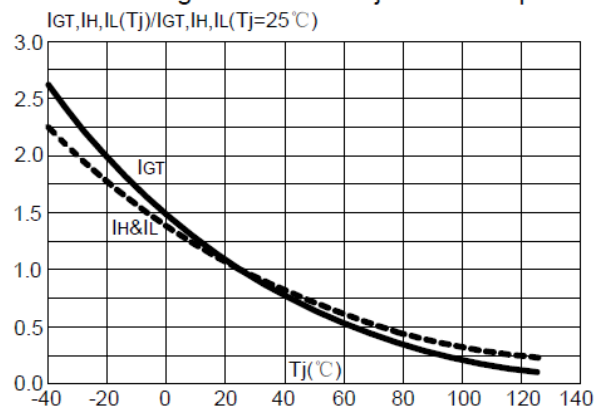


FIG.5: Gate trigger characteristics
(per thyristor or diode)

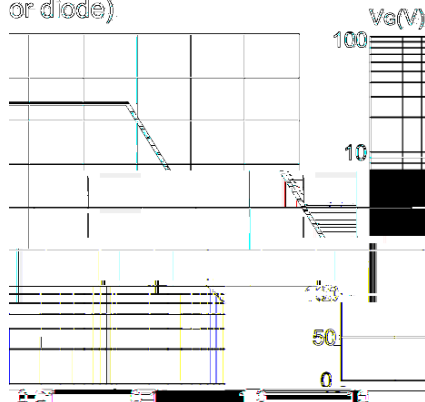


FIG.6: Forward current vs. case temperature

